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(54) **SEMICONDUCTOR STRUCTURE AND  
MANUFACTURING METHOD THEREOF**

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(57) **ABSTRACT**

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The present disclosure relates to a semiconductor structure and a manufacturing method thereof. The semiconductor structure includes: a substrate, including a first region and a second region that are adjacent to each other; an array structure, located on a surface of the substrate and on the first region; a conductive layer, located on a side of the array structure that is away from the substrate and electrically connected to the array structure; a wiring structure, located on a side of the conductive layer that is away from the array structure, where the wiring structure includes a re-wiring through hole, and the re-wiring through hole is electrically connected to the conductive layer; and a first dielectric layer, covering a surface of the second region of the substrate.

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